2SD1775, 2SD1775A

Silicon NPN triple diffusion planar type

For high-speed switching and high current amplification ratio

Features

- High foward current transfer ratio h_{FE}
- Satisfactory linearity of foward current transfer ratio h_{FE}
- N type package enabling direct soldering of the radiating fin to the printed circuit board, etc. of small electronic equipment.

Absolute Maximum Ratings (T_C=25°C)

Parameter		Symbol	Ratings	Unit	
Collector to	2SD1775	V	80	v	
base voltage	2SD1775A	V_{CBO}	100		
Collector to	2SD1775	V	60	V	
emitter voltage	2SD1775A	V_{CEO}	80	V	
Emitter to base voltage		V _{EBO}	6	V	
Peak collector current		I_{CP}	4	A	
Collector current		$I_{\rm C}$	2	Α	
Base current		I_B	0.5	A	
Collector power	T _C =25°C	D	25	777	
dissipation	Ta=25°C	P_{C}	1.3	W	
Junction temperature		T_{j}	150	°C	
Storage temperature		$T_{\rm stg}$	-55 to +150	90.C	

Unit: mm 1.0±0.1 1.1max. 0.5max. 1:Base 2:Collector 3:Emitter N Type Package Unit: mm 1.0±0.1 0.8±0.1 2.54±0.3 1:Base 2:Collector 3:Emitter N Type Package (DS)

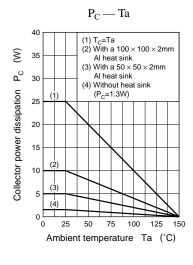
Electrical Characteristics (T_C=25°C)

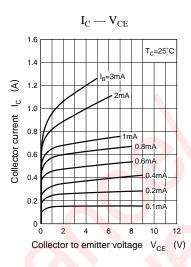
Parameter		Symbol	Conditions	min	typ	max	Unit
Collector cutoff	2SD1775	1 (1)	$V_{CB} = 80V, I_E = 0$	100	9	100	μА
current	2SD1775A	I _{CBO}	$V_{CB} = 100V, I_E = 0$	000		100	
Collector cutoff current		I_{CEO}	$V_{CE} = 40V, I_{B} = 0$	$-O_{L/L}$		100	μА
Emitter cutoff curren	t 🔊	I_{EBO}	$V_{EB} = 6V, I_C = 0$			100	μΑ
Collector to emitter	2SD1775	V _{CEO}	$I_{\rm C} = 25 {\rm mA}, I_{\rm B} = 0$	60			v
voltage	2SD1775A			80			
Forward current transfer ratio		h _{FE} *	$V_{CE} = 4V, I_{C} = 300mA$	500		1500	
Collector to emitter saturation voltage		V _{CE(sat)}	$I_C = 1A, I_B = 25mA$			1.0	V
Base to emitter saturation voltage		V _{BE(sat)}	$I_C = 1A, I_B = 25mA$			1.2	V
Transition frequency		f_T	$V_{CE} = 12V, I_{C} = 200mA, f = 10MHz$		40		MHz
Collector output capacitance		C _{ob}	$V_{CB} = 10V, I_E = 0, f = 1MHz$		30		pF
Turn-on time		t _{on}	$I_C = 1A$, $I_{B1} = 25mA$, $I_{B2} = -25mA$,		0.6		μs
Storage time		t _{stg}			2.5		μs
Fall time		$t_{\rm f}$	$V_{CC} = 50V$		1.0		μs

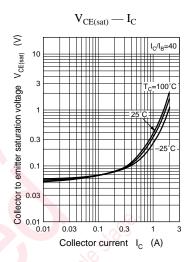
*h_{FE} Rank classification

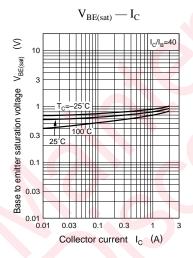
Rank	Q	P
h_{FE}	500 to 1000	800 to 1500

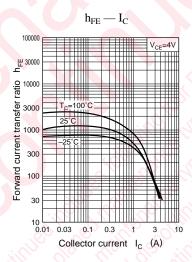
Panasonic 1

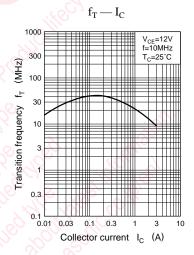


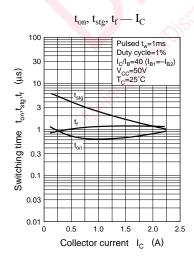


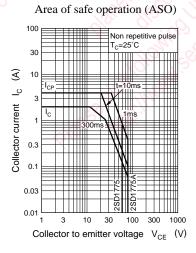


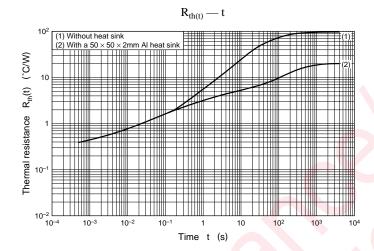












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